

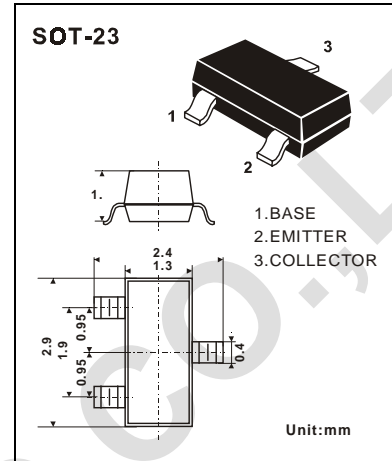
NPN EPITAXIAL SILICON TRANSISTOR

* Complement to 2SA1015

* Collector Current : $I_c=150\text{mA}$

ABSOLUTE MAXIMUM RATINGS at $T_a=25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	60	V
Collector-Emitter Voltage	V_{ceo}	50	V
Emitter-Base Voltage	V_{ebo}	5	V
Collector Current	I_c		mA
Collector Dissipation $T_a=25^\circ\text{C}^*$	P_D	225	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS at $T_a=25^\circ\text{C}$

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{cbo}	60			V	$I_c=100\mu\text{A}$ $I_e=0$
Collector-Emitter Breakdown Voltage#	BV_{ceo}	50			V	$I_c=1\text{mA}$ $I_b=0$
Emitter-Base Breakdown Voltage	BV_{ebo}	5.0			V	$I_e=100\mu\text{A}$ $I_c=0$
Collector-Base Cutoff Current	I_{cbo}			100	nA	$V_{cb}=50\text{V}$ $I_e=0$
Emitter-Base Cutoff Current	I_{ebo}			100	nA	$V_{eb}=3\text{V}$ $I_c=0$
DC Current Gain	H_{fe}	70		700		$V_{ce}=6\text{V}$ $I_c=2\text{mA}$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.30	V	$I_c=100\text{mA}$ $I_b=10\text{mA}$

* Total Device Dissipation : $FR=1 \times 0.75 \times 0.062\text{in Board}$, Derate 25°C .

Pulse Test : Pulse Width $\leq 300\mu\text{S}$, Duty cycle $\leq 2\%$

DEVICE MARKING:

2SC1815=L6